

Doping behaviors of NiO and Nb₂O₅ in BaTiO₃ and dielectric properties of BaTiO₃-based X7R ceramics

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Received 28 June 2011; received in revised form 9 October 2011; accepted 10 October 2011

Available online 15 October 2011

Abstract

Doping behaviors of NiO and Nb₂O₅ in BaTiO₃ in two doping ways and dielectric properties of BaTiO₃-based X7R ceramics were investigated. When doped in composite form, the additions rendered higher solubility than that doped separately due to the identical valence between the complex (Ni_{1/3}²⁺Nb_{2/3}⁵⁺)⁴⁺ and Ti⁴⁺. NiO–Nb₂O₅ composite oxide was more effective in broadening dielectric constant peaks which was responsible for the temperature-stability of BaTiO₃ ceramics. A reduction in grain size was observed in the specimens with 0.5–0.8 mol% NiO–Nb₂O₅ composite oxide, whereas the abnormal growth of individual grains took place in the 1.0 mol% NiO–Nb₂O₅ composite oxide-doped specimen. When the specimen of BaTiO₃ doped with 0.8 mol% NiO–Nb₂O₅ composite oxide was sintered at 1300 °C for 1.5 h in air, good dielectric properties were obtained and the requirement of (EIA) X7R specification with a dielectric constant of 4706 and dielectric loss lower than 1.5% were satisfied.

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Keywords: BaTiO₃; NiO–Nb₂O₅ composite oxide; Solubility; Broadening peaks; X7R

1. Introduction

X7R multi-layer ceramic capacitors (MLCCs) have been widely used for miniaturization of electronic components. BaTiO₃-based X7R dielectric materials mainly used to prepare MLCCs had attracted much attention due to their high permittivity and excellent dielectric constant thermal stability (–55 °C to 125 °C, $\Delta C/C \leq 15\%$).

Many investigations have been performed in order to obtain a superior material with high dielectric constant and X7R characteristics. The commonly used methods for improving the dielectric properties of BaTiO₃ include incorporation of additives (Nb₂O₅, MgO, Co₂O₃ and Yb₂O₃) [1–4], specialized synthesis of BaTiO₃ [5,6] and grain size distribution [7–9] and sintering process [10,11]. It has been known that achieving a good dielectric property through addition of dopants was most commonly used by researchers, such as BaTiO₃–Nb₂O₅–ZnO [12], BaTiO₃–Nb₂O₅–Co₃O₄ [13], and BaTiO₃–Nb₂O₅–Ni₂O₃ [14] systems. As many researchers have reported [15–18], NiO

and Nb₂O₅ additions can broaden dielectric constant peaks and improve dielectric properties of BaTiO₃-based ceramics. However, doping Nb₂O₅, NiO in the form of composite oxide showed great effects in improving dielectric properties of the BaTiO₃ ceramics compared to doping Nb₂O₅, NiO separately, which has not been reported.

In this paper, the solubility of NiO, Nb₂O₅ in BaTiO₃ and the effects on dielectric peak-broadening of BaTiO₃ by two doping methods (doping NiO–Nb₂O₅ as composite oxide and doping NiO, Nb₂O₅ separately) was investigated. The doping mechanism of NiO, Nb₂O₅ and the dielectric peak-broadening mechanism of NiO–Nb₂O₅ composite oxide in BaTiO₃-based system were elucidated precisely. Moreover, through the first doping methods, the BaTiO₃-based X7R ceramic with satisfactory dielectric properties was synthesized using conventional mixed-oxide method, which can help develop novel temperature-stable dielectric materials for X7R MLCCs.

2. Experimental procedure

BaTiO₃ (particle size about 0.4 μm) powders were synthesized by co-precipitation method and calcined at 1080 °C for 2 h. Nb₂O₅ (99.99%, Jiujiang Tanbre's Smeltery,

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China), NiO (99.0%, Tianjin Chemical Reagent Company, China) were used as the starting materials. NiO and Nb₂O₅ powders were mixed and milled in deionized water and zirconia milling media for 4 h, then dried and calcined at 1000 °C for 2 h to form NiO–Nb₂O₅ composite oxide. The NiO–Nb₂O₅ composite oxide powders and BaTiO₃ were milled again and dried to form composite (hereafter referred to as composition A). The uncalcined NiO and Nb₂O₅ were milled with BaTiO₃ directly and dried to form composite (hereafter referred to as composition B). The milled powders were granulated by mixing them with a 7 wt.% binder, and then the granules were pressed into disks with 20 mm in diameter and 1 > 1.5 mm in thickness. These samples were conventionally sintered at 1300 °C in air for 1.5 h.

After samples were fired at 850 °C with Ag electrodes on both surfaces, the capacitances of samples were measured from –55 °C to 150 °C with LCR (HP4278A) at 1 kHz and 1 V rms. The temperature was controlled by GZ-ESPEC oven. The dielectric constant (ϵ_r) and the variation of capacity ($\Delta C/C_{20\text{ }^\circ\text{C}}$ (%)) were calculated from the measured capacitances. Insulation resistance was measured using a high resistance meter (Super-High Resistance Meter Model ZC36) at room temperature. D/MAX-B Model X-ray diffractometer with Cu K α radiation at 40 kV and 40 mA settings was used to analyze the phase composition of ceramics. The dielectric loss was measured at 1 kHz with LCR (HP4278A). Microstructural properties such as grain size distribution and morphology were examined using a Phillips XL30 scanning electron microscope (SEM).

3. Results and discussion

3.1. Solubility analysis

Fig. 1(a) and (b) shows the XRD patterns of composition A (doping NiO, Nb₂O₅ as composite oxide) and composition B (doping NiO, Nb₂O₅ separately) samples sintering at 1300 °C for 1.5 h, respectively. The compositions of A1–A4 and B1–B4 were shown in Table 1.

The X-ray diffraction patterns of composition A and composition B both showed a pseudo-cubic structure with a single peak of (2 0 0). The secondary phase (Ba₆Ti₁₇O₄₀ (JCPDF 77-1566)) was detected when 1.0 mol% NiO–Nb₂O₅ composite oxide was added to BaTiO₃, while it was already observed when NiO, Nb₂O₅ were added separately at 0.8 mol%. Therefore, it was indicated that the solubility limit of NiO, Nb₂O₅ in BaTiO₃ were different between the two different doping methods. NiO, Nb₂O₅ had relatively larger solubility limit by doping NiO, Nb₂O₅ as composite oxide.

When NiO, Nb₂O₅ were compounded into BaTiO₃-based ceramics system, Ni²⁺ and Nb⁵⁺ were apt to replace Ti⁴⁺ due to their similar ionic radius [17–20]. The effects of Nb and Ni elements were different. Since the charge of Ni²⁺ ion was lower than that of Ti⁴⁺ ion, the Ni²⁺ ion acted as an acceptor to BaTiO₃, whereas Nb element was a donor for its relatively

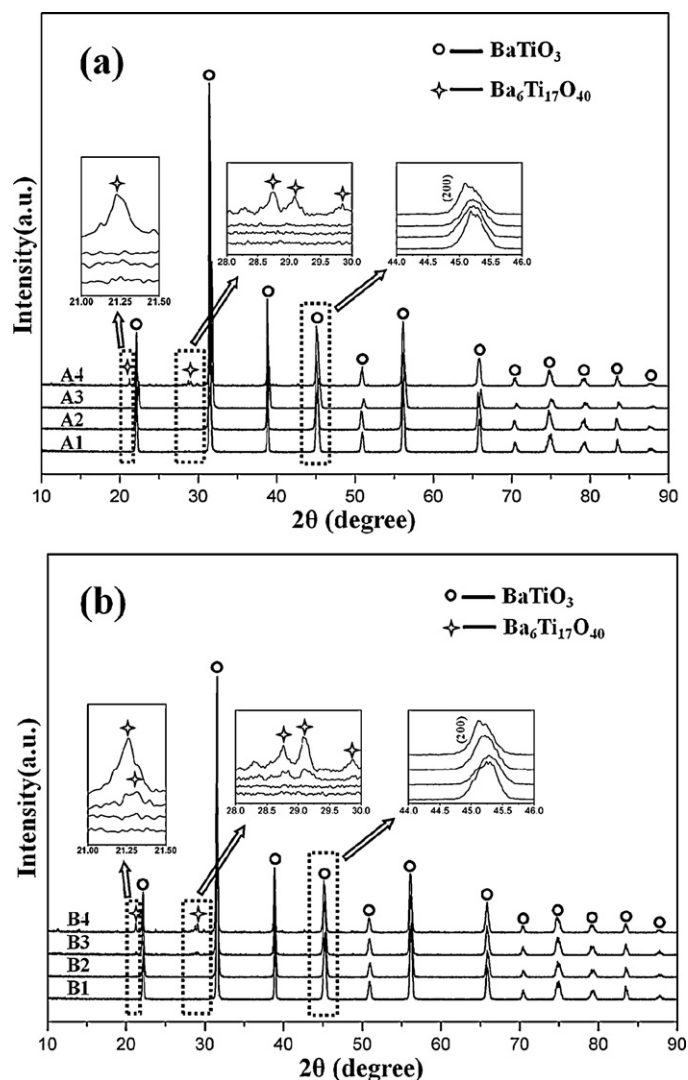


Fig. 1. XRD patterns of samples (a) composition A (A1–A4) and (b) composition B (B1–B4) sintered at 1300 °C.

higher valence. The defect reactions were shown as follows:

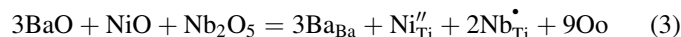


Table 1
Sample compositions (mol%).

Composition	BaTiO ₃	Nb ₂ O ₅	NiO
A1	100	0.5 NiO–0.5 Nb ₂ O ₅ composite oxide	
A2	100	0.7 NiO–0.7 Nb ₂ O ₅ composite oxide	
A3	100	0.8 NiO–0.8 Nb ₂ O ₅ composite oxide	
A4	100	1.0 NiO–1.0 Nb ₂ O ₅ composite oxide	
B1	100	0.5	0.5
B2	100	0.7	0.7
B3	100	0.8	0.8
B4	100	1.0	1.0

In composition B, the low solubility of NiO, Nb₂O₅ in BaTiO₃ was related to different valence states among Ni²⁺, Nb⁵⁺ and Ti⁴⁺. The differences of valence among Ni²⁺, Nb⁵⁺ and Ti⁴⁺ ions resulted in the appearance of the vacancies, as Eqs. (1) and (2) shown. The generation of vacancies resulted in the distortion of the lattice. With larger lattice distortion, the energy of lattice distortion would be higher, which led to instability of the crystal structure. And the instability limited the further diffusion of the doping ions [21], which resulted in the relatively low solubility of NiO, Nb₂O₅ in BaTiO₃ of composition B.

In composition A, when NiO and Nb₂O₅ were doped as NiO–Nb₂O₅ composite oxide, the Ni²⁺ and Nb⁵⁺ ions would replace the Ti⁴⁺ by forming the composite cation of (Ni_{1/3}²⁺Nb_{2/3}⁵⁺)⁴⁺. The ionic radius of (Ni_{1/3}²⁺Nb_{2/3}⁵⁺)⁴⁺ was close to the radius of Ti⁴⁺ (The effective radius of Ti⁴⁺ was 0.061 nm and (Ni_{1/3}²⁺Nb_{2/3}⁵⁺)⁴⁺ was 0.066 nm in the 6-fold coordination [22]). Furthermore, the valence of the complex (Ni_{1/3}²⁺Nb_{2/3}⁵⁺)⁴⁺ was identical to Ti⁴⁺. When NiO and Nb₂O₅ were doped in BaTiO₃ as composite, the ions Ni²⁺ and Nb⁵⁺ substituted Ti site as follows:



This reaction may exclude the energetically unfavorable defect species such as V_{Ti}^{\bullet} in Eq. (2). Thus, the composite source of NiO and Nb₂O₅ creates favorable defect species as shown in Eq. (3), leading to higher solubility in composition A.

3.2. Dielectric peak-broadening effects

Fig. 2(a) and (b) presents the temperature dependence of the dielectric constant ϵ_r of the composition A (A1–A4) and composition B (B1–B4) ceramics measuring at 1 kHz.

Two dielectric constant peaks were observed in the dielectric constant–temperature curves (ϵ_r – T curves) in Fig. 2(a) and (b). This phenomenon was associated with the chemically inhomogeneous structure (the “core–shell” structure) of doped BaTiO₃. The Curie dielectric peak (at about 130 °C) was determined by the ferroelectric–paraelectric transition of grain core, whereas the secondary peak at lower temperature was due to strong chemical inhomogeneity of grain shell [23]. It was apparent that the flattening ability of additives in this system was associated with the inhomogeneous chemical distribution of grain shell in the matrix grains.

It was apparent that the secondary dielectric constant peak was more obvious and broader in Fig. 2(a) than in Fig. 2(b). The results indicate that the NiO–Nb₂O₅ composite oxide was very effective to flatten the dielectric constant–temperature curve at low temperature. Since the (Ni_{1/3}²⁺Nb_{2/3}⁵⁺)⁴⁺ cation easily diffused into the crystal lattice in composition A to form the chemically inhomogeneous structure of grain shell. A relatively large volume fraction of the grain shell resulted in the obvious dielectric constant peak at low temperature.

As show in Fig. 2(a), the ϵ_r – T curves became broader with the increasing amount of (Ni_{1/3}²⁺Nb_{2/3}⁵⁺)⁴⁺ addition (from 0.5 mol% to 1.0 mol%). A certain amount of (Ni_{1/3}²⁺Nb_{2/3}⁵⁺)⁴⁺ ions substituting for Ti⁴⁺ ions formed the chemically

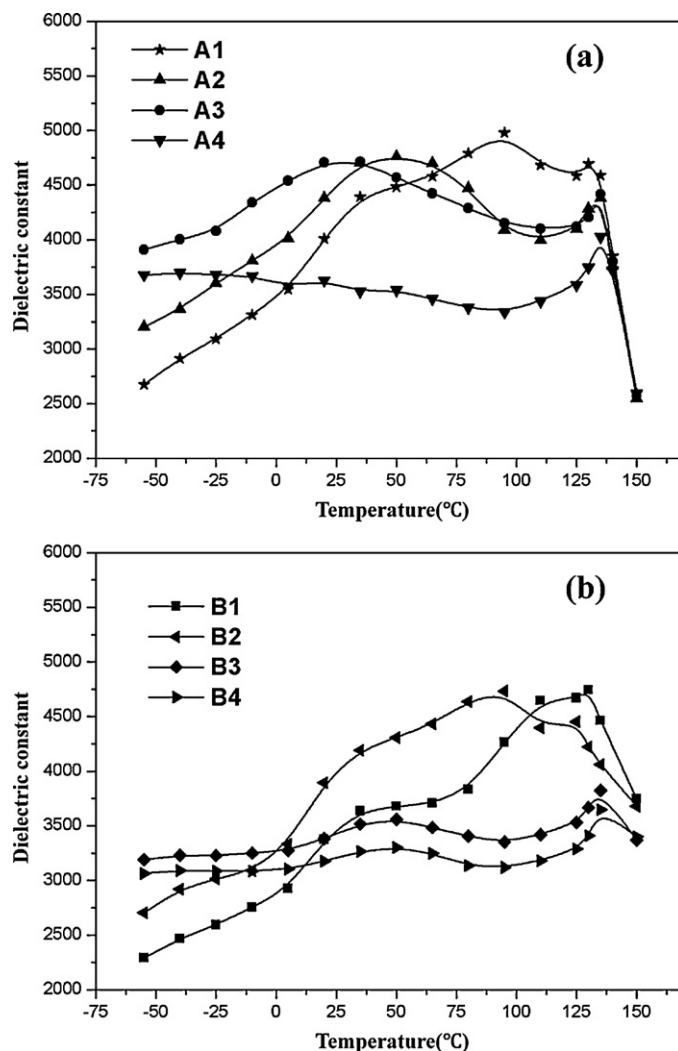


Fig. 2. Temperature dependence of dielectric constant of samples (a) composition A (A1–A4) and (b) composition B (B1–B4) sintered at 1300 °C for 1.5 h.

inhomogeneous structure and the compositional inhomogeneity might induce diffuse phase transition characteristics, which resulted in a multi-peaks character over a relatively wide temperature range. The combination and overlapping of multi-peaks contributed to the broad peaks of ϵ_r – T curves. And the diffuse phase transition behavior of this system became more pronounced with increasing amount of (Ni_{1/3}²⁺Nb_{2/3}⁵⁺)⁴⁺. So the overall dielectric peaks of compositions A was broadened in the whole measurement temperature when the amount of (Ni_{1/3}²⁺Nb_{2/3}⁵⁺)⁴⁺ increased.

3.3. Microstructure and dielectric properties of composition A

According to the previous discussion, composition A showed a preferable dielectric peaks broadening effect, which was helpful to improve the dielectric properties of BaTiO₃-based ceramics. Therefore, the microstructure and dielectric properties of composition A samples would be further analyzed.

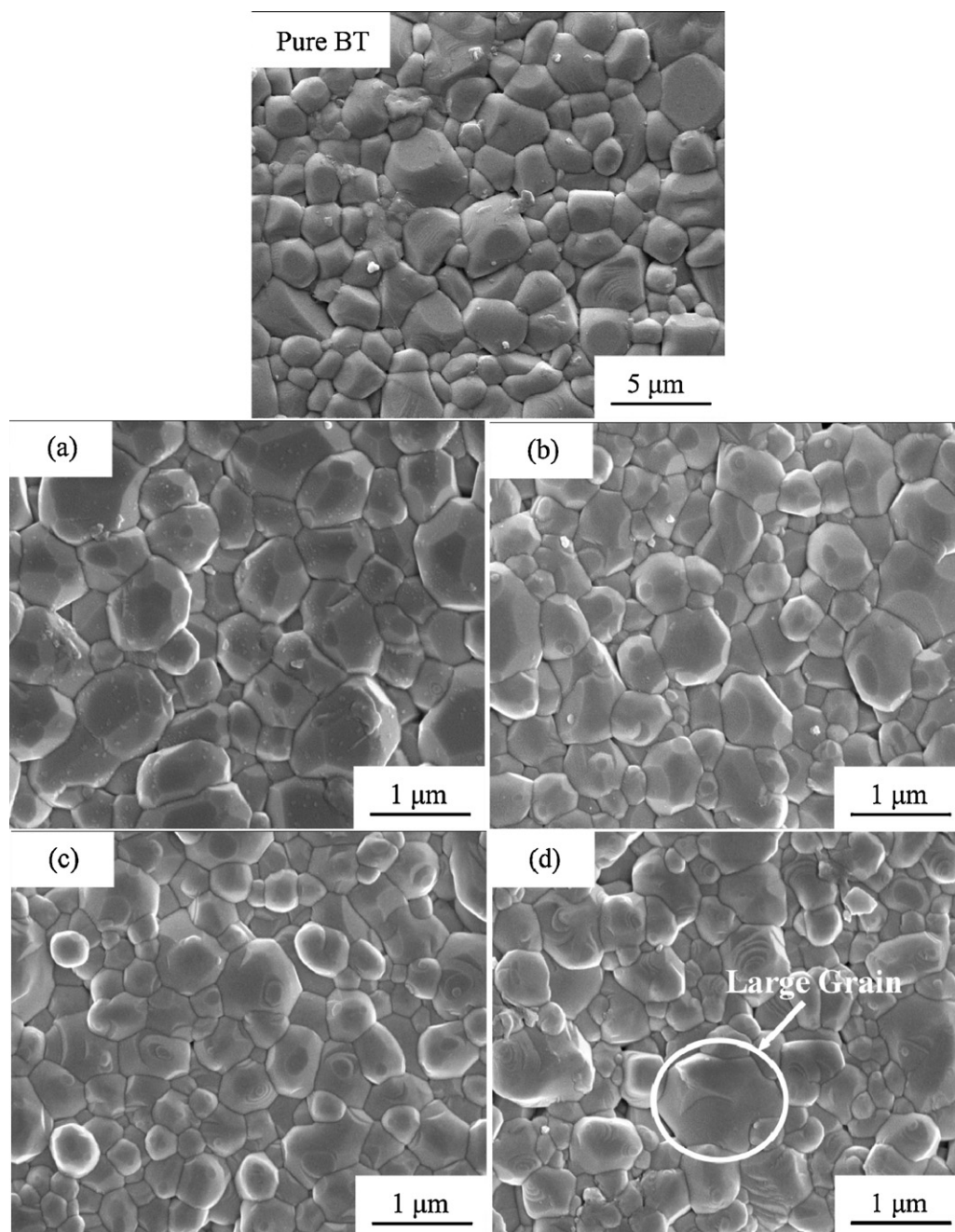


Fig. 3. SEM micrographs of pure BaTiO₃ and composition A (A1–A4): (a) A1, (b) A2, (c) A3, (d) A4 samples sintered at 1300 °C.

Fig. 3 showed the microstructures of pure BaTiO₃ and composition A specimens after sintering at 1300 °C for 1.5 h in air. The average grain sizes of sintered ceramics were obtained from the SEM micrographs by the linear interception method [24], as shown in Table 2. The average size of BaTiO₃ grains in the pure BaTiO₃ specimens grew to 2.62 μm. With increasing additions content, the grains of the samples became more perfect and the grain sizes decreased, when the content of NiO–Nb₂O₅ composite oxide was less than 0.8 mol%, indicating that the addition of the (Ni_{1/3}²⁺Nb_{2/3}⁵⁺)⁴⁺ ions inhibited the grain growth of BaTiO₃ in these samples. However, when the NiO–Nb₂O₅ composite oxide content increased further to 1.0 mol%, a slight increase in average grain size was observed in Table 2.

Table 2

Average grain sizes of pure BaTiO₃ and composition A (A1–A4) samples sintered at 1300 °C for 1.5 h.

Samples	Average grain size (μm)
Pure BT	2.62
A1	0.76
A2	0.61
A3	0.53
A4	0.56

Table 3
Dielectric properties of composition A (A1–A4) samples.

Samples	Dielectric constant (ϵ_r)	Dielectric loss (tg δ %)	Insulation resistance (ρ_v , $10^{12} \Omega \text{ cm}$)	Temperature coefficient of capacitance ($\Delta C/C_{20^\circ\text{C}}$ (%))	
				–55 °C	125 °C
A1	4010	1.732	2.1	–33.2	14.2
A2	4380	1.356	2.8	–26.8	–6.4
A3	4706	1.230	3.7	–14.6	–12.5
A4	3627	0.838	5.0	1.3	–1.1

This was related to the formation of individual large grains as shown in Fig. 3(d). As NiO–Nb₂O₅ composite oxide content increased to 1.0 mol%, secondary phase began to occur which was proved by XRD analysis. However, it was hard to observe the secondary phase grains by SEM due to the formation of small amount of secondary phase. The formation of liquid phase of Ba₆Ti₁₇O₄₀, might be responsible for the formation of large grains.

The main dielectric properties of composition A specimens were summarized in Table 3. The dielectric constant (ϵ_r) at room temperature initially increased with increasing NiO–Nb₂O₅ composite oxide content up to 0.8 mol% and then decreased. Consequently, the sample with 0.8 mol% composite oxide had ϵ_r as high as 4706, which was higher than that of the BaTiO₃–Ni₂O₃–Nb₂O₅ system [14]. The high dielectric constant was related to the second broad peak near room temperature and homogeneous fine-grained microstructures as shown in Fig. 3(c). When NiO–Nb₂O₅ composite oxide content increased to 1.0 mol%, room temperature constant decreased pronouncedly. This was related to the increase of non-ferroelectric phase of grain shell and the abnormal growth of individual grain for the emergence of the secondary phase, when the amount of NiO–Nb₂O₅ composite oxide added was beyond the solubility.

The room temperature dielectric loss (tg δ) monotonically decreased with increasing content of NiO–Nb₂O₅ composite oxide. This was owing to the polarization actually decreased

due to the substitution between Ti⁴⁺ and (Ni_{1/3}Nb_{2/3})⁴⁺ and small ionic polarization led to the decrease in dielectric loss. For the samples doped with 0.7, 0.8, 1.0 mol% NiO–Nb₂O₅ composite oxide, dielectric loss values were less than 1.5% and the insulation resistances were higher than $10^{12} \Omega \text{ cm}$.

$\Delta C/C_{20^\circ\text{C}}-T$ curves of composition A ceramics were presented in Fig. 4. The $\Delta C/C_{20^\circ\text{C}}-T$ curves were flattened and peaks were broadened noticeably with the amount of additions increasing. Especially the variation rate of capacity of samples with 0.8 mol% NiO–Nb₂O₅ composition doping was already lower than $\pm 15\%$, which satisfied the X7R specification with a high dielectric constant. The sample exhibited satisfied variation of capacity when the amount of dopants increased up to 1.0 mol%, but the room temperature dielectric constant was relatively low about 3600.

It can conclude that the ceramics with 0.8 mol% NiO–Nb₂O₅ composition oxide content had the maximum room temperature permittivity (4706) and the low dielectric loss (0.0123). The ceramic had better dielectric temperature stability with the temperature ranging from –55 °C to 125 °C, and satisfied the specification of (EIA) X7R capacitor. The NiO–Nb₂O₅ composite oxide was very helpful in improving the overall dielectric properties of BaTiO₃-based ceramics.

4. Conclusions

Doping behaviors of NiO and Nb₂O₅ in BaTiO₃ and dielectric properties of BaTiO₃-based X7R ceramics have been investigated. When NiO and Nb₂O₅ doped as composite oxide, the Ni²⁺, Nb⁵⁺ cations would replace the Ti site by forming the composite cation of (Ni_{1/3}²⁺Nb_{2/3}⁵⁺)⁴⁺. From the solubility analysis results, Ni²⁺, Nb⁵⁺ cations were easier to diffuse into the crystal lattice by using the NiO–Nb₂O₅ composite oxide as dopants, which was attributed to the identity of (Ni_{1/3}²⁺Nb_{2/3}⁵⁺)⁴⁺ and Ti⁴⁺. NiO and Nb₂O₅ doping as composite oxide were more effective in broadening dielectric peaks and improving dielectric properties of the BaTiO₃-based ceramics. With increasing NiO–Nb₂O₅ composition oxide content (from 0.5 mol% to 0.8 mol%), the grain size of BaTiO₃ decreased, whereas the abnormal growth of individual grains took place in the 1.0 mol% composition oxide-doped specimen. The abnormal growth in grain size was related to presence of the second phase, Ba₆Ti₁₇O₄₀. When the amount of NiO–Nb₂O₅ composite oxide was up to 0.8 mol%, a good dielectric property was achieved and satisfied the requirement of (EIA) X7R

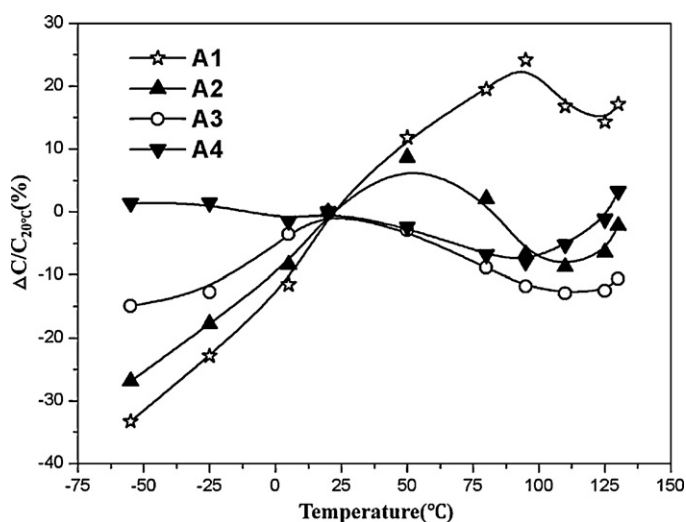


Fig. 4. $\Delta C/C_{20^\circ\text{C}}-T$ curves of composition A (A1–A4) samples.

specification with dielectric constant as high as 4706 and dielectric loss lower than 1.5%. This material is promising for preparing X7R MLCCs with large capacitances.

Acknowledgments

This work was supported by Program for New Century Excellent Talents in University (NCET) and 863 program (2007AA03Z423).

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